

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (currently amended): A semiconductor with integrated monitoring comprising:

a first light emitting semiconductor device formed on a predetermined substrate;
a passivation layer formed on top of said first semiconductor device, said passivation layer including a window; and
a light monitoring device formed on top of said passivation layer for monitoring leakage light from said first semiconductor device through said window.

Claim 2 (original): The semiconductor as recited in claim 1, wherein said first semiconductor device is an active device.

Claim 3 (currently amended): ~~A~~ The semiconductor ~~with integrated monitoring comprising:~~

~~—— a first semiconductor formed on~~ as recited in claim 1, wherein said predetermined substrate is a GaAs substrate;
~~—— a passivation layer formed on top of said first semiconductor device; and~~
~~—— a monitoring device formed on top of said passivation layer.~~

Claim 4 (currently amended): ~~A~~ The semiconductor ~~with integrated monitoring comprising:~~

~~—— a first semiconductor formed on~~ as recited in claim 1, wherein said predetermined substrate is a InP substrate;
~~—— a passivation layer formed on top of said first semiconductor device; and~~
~~—— a monitoring device formed on top of said passivation layer.~~

Claim 5 (currently amended): ~~A~~ The semiconductor ~~with integrated monitoring comprising:~~

~~—— a first semiconductor formed on~~ as recited in claim 1, wherein said predetermined substrate is a GaN substrate;
~~—— a passivation layer formed on top of said first semiconductor device; and~~

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~~_____a monitoring device formed on top of said passivation layer.~~

Claim 6 (cancelled)

Claim 7 (original): The semiconductor as recited in claim 1, wherein said first semiconductor device is a light emitting device.

Claim 8 (original): The semiconductor as recited in claim 6, wherein said light emitting device is a laser.

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Claim 9 (original): The semiconductor as recited in claim 8, wherein said laser is a vertical cavity surface emitting laser (VCSEL).

112 Claim 10 (original): The semiconductor as recited in claim 1, wherein said monitoring device is a light transmitting device.

Claim 11 (original): The semiconductor as recited in claim 1, wherein said monitoring device is a light receiving device.

Claim 12 (original): The semiconductor as recited in claim 10, wherein said light transmitting device is a photodiode.

Claim 13 (original): The semiconductor as recited in claim 11, wherein said light receiving device is a photodetector.

Claims 14-22 (cancelled)
